NVD5867NL

Power MOSFET

60 V, 22 A, 39 mΩ, Single N−Channel

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- High Current Capability
- Avalanche Energy Specified
- AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

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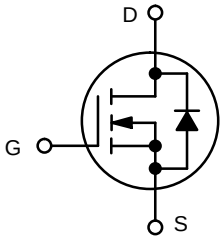
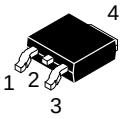
$V_{(BR)DSS}$	$R_{DS(on)}$	I_D
60 V	39 mΩ @ 10 V	22 A
	50 mΩ @ 4.5 V	



N−CHANNEL MOSFET



DPAK
CASE 369AA
STYLE 2

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	60	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1 & 3)	Steady State	T_C = 25°C	I_D	22	A
		T_C = 100°C		16	
Power Dissipation $R_{\theta JC}$ (Note 1)		T_C = 25°C	P_D	43	W
		T_C = 100°C		21	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2 & 3)	Steady State	T_A = 25°C	I_D	6.0	A
		T_A = 100°C		4.0	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)		T_A = 25°C	P_D	3.3	W
		T_A = 100°C		1.7	
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	85	A
Current Limited by Package (Note 3)	T_A = 25°C		$I_{Dmaxpkg}$	30	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to 175	°C
Source Current (Body Diode)			I_S	36	A
Single Pulse Drain−to−Source Avalanche Energy (T_J = 25°C, V_{DD} = 50 V, V_{GS} = 10 V, $I_{L(pk)}$ = 19 A, L = 0.1 mH, R_G = 25 Ω)			E_{AS}	18	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

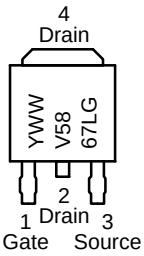
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Drain) (Note 1)	$R_{\theta JC}$	3.5	°C/W
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	45	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface−mounted on FR4 board using a 650 mm^2, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

MARKING DIAGRAM & PIN ASSIGNMENT



Y = Year
WW = Work Week
V5867L = Device Code
G = Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		60			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				60		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 60 V	T_J = 25°C			1.0	μA
			T_J = 125°C			100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.5	1.8	2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				5.2		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 11 A			26	39	mΩ
		V_{GS} = 4.5 V, I_D = 11 A			33	50	
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 11 A			8.0		S
CHARGES, CAPACITANCES AND GATE RESISTANCES							
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 25 V			675		pF
Output Capacitance	C_{oss}				68		
Reverse Transfer Capacitance	C_{rss}				47		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 48 V, I_D = 22 A			15		nC
Threshold Gate Charge	$Q_{G(TH)}$				1.0		
Gate−to−Source Charge	Q_{GS}				2.2		
Gate−to−Drain Charge	Q_{GD}				4.3		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 48 V, I_D = 22 A			7.6		nC
Gate Resistance	R_G				1.3		Ω
SWITCHING CHARACTERISTICS (Note 5)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 10 V, V_{DD} = 48 V, I_D = 22 A, R_G = 2.5 Ω			6.5		ns
Rise Time	t_r				12.6		
Turn−Off Delay Time	$t_{d(off)}$				18.2		
Fall Time	t_f				2.4		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 10 A	T_J = 25°C		0.87	1.2	V
			T_J = 125°C		0.78		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dIs/dt = 100 A/μs, I_S = 22 A			17		ns
Charge Time	ta				13		
Discharge Time	tb				4.0		
Reverse Recovery Charge	Q_{RR}				12		nC

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

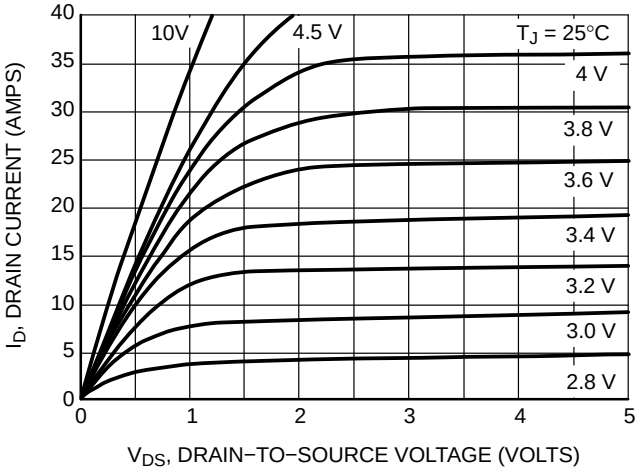


Figure 1. On−Region Characteristics

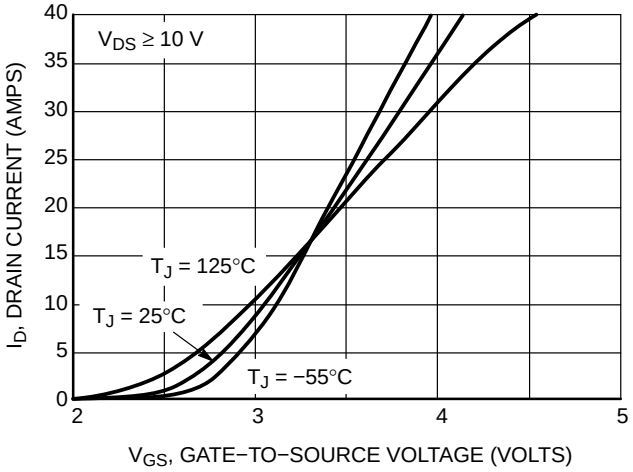


Figure 2. Transfer Characteristics

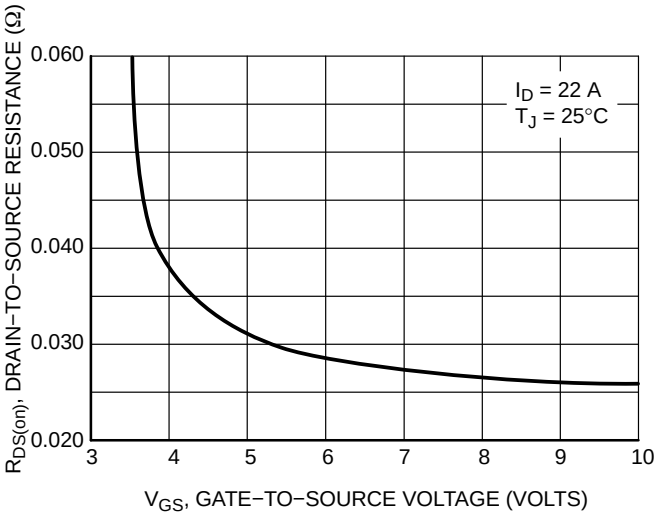


Figure 3. On−Resistance vs. Gate−to−Source Voltage

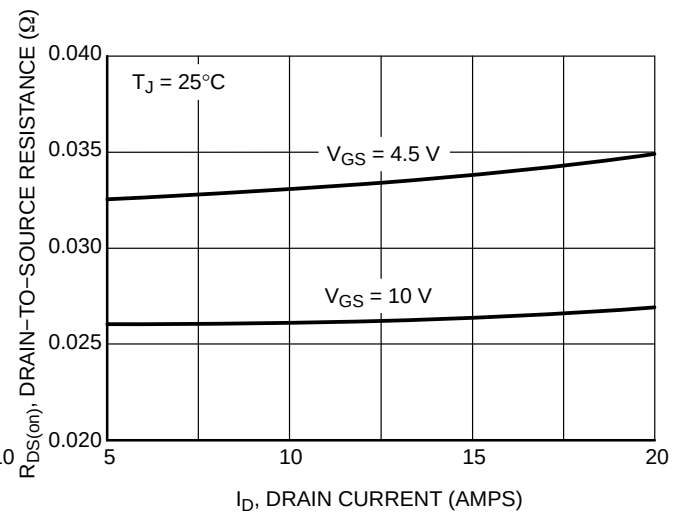


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

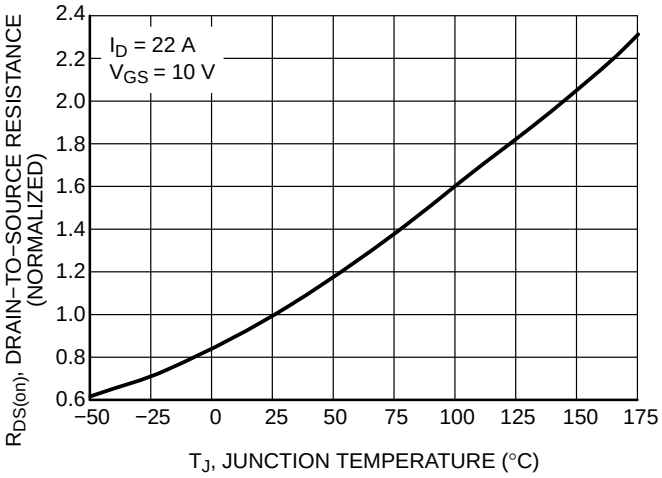


Figure 5. On−Resistance Variation with Temperature

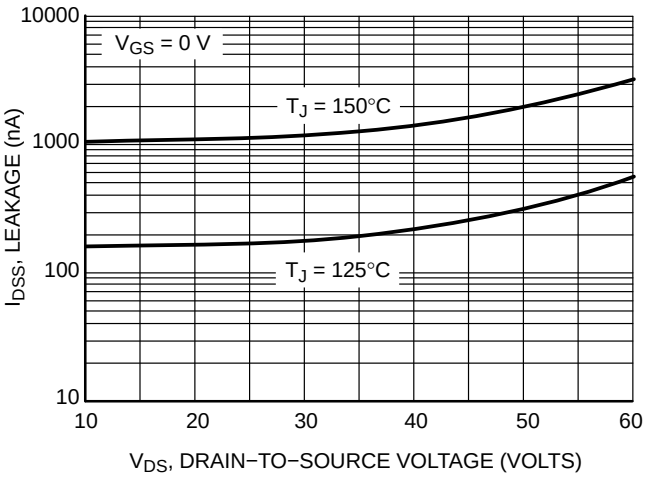


Figure 6. Drain−to−Source Leakage Current vs. Drain Voltage

TYPICAL PERFORMANCE CURVES

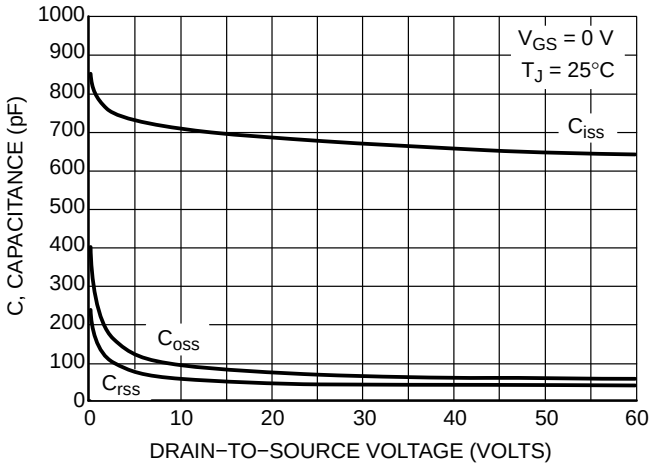


Figure 7. Capacitance Variation

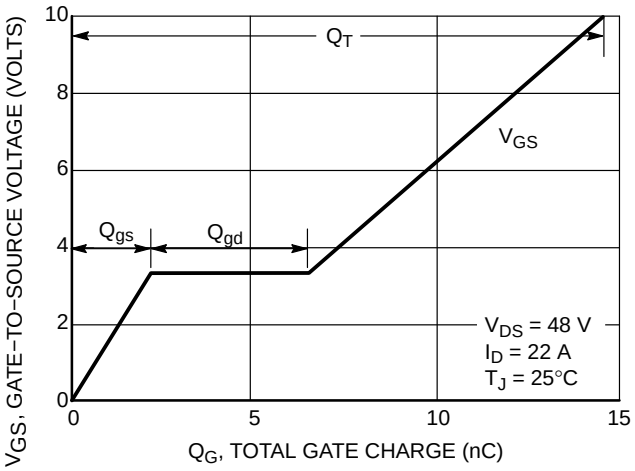


Figure 8. Gate−To−Source Voltage vs. Total Charge

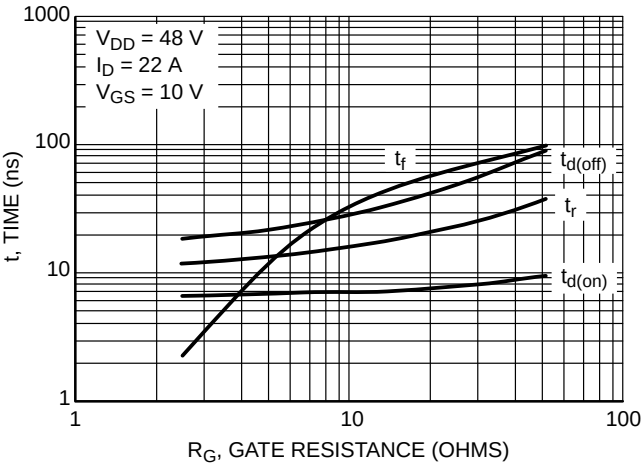


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

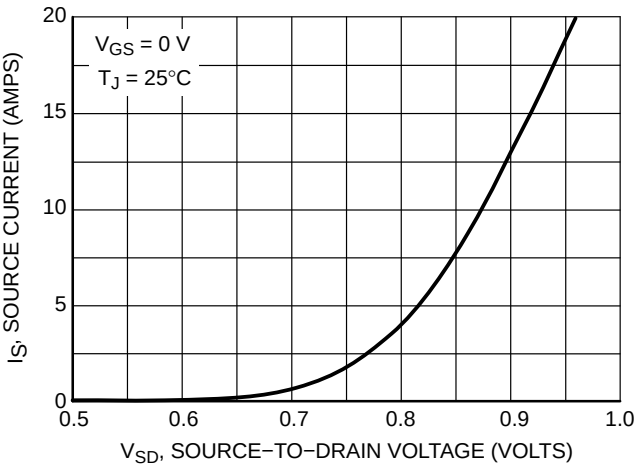


Figure 10. Diode Forward Voltage vs. Current

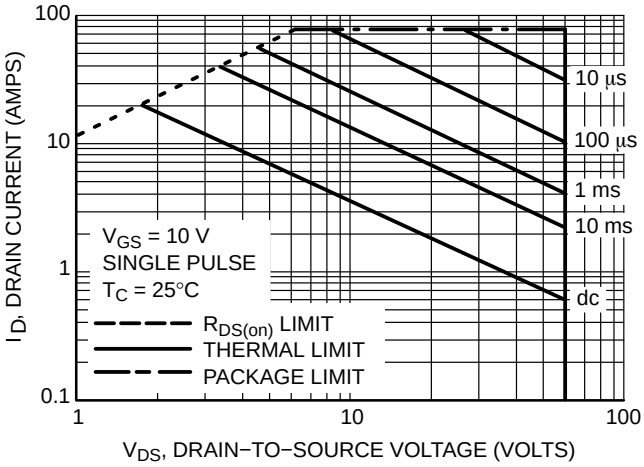


Figure 11. Maximum Rated Forward Biased Safe Operating Area

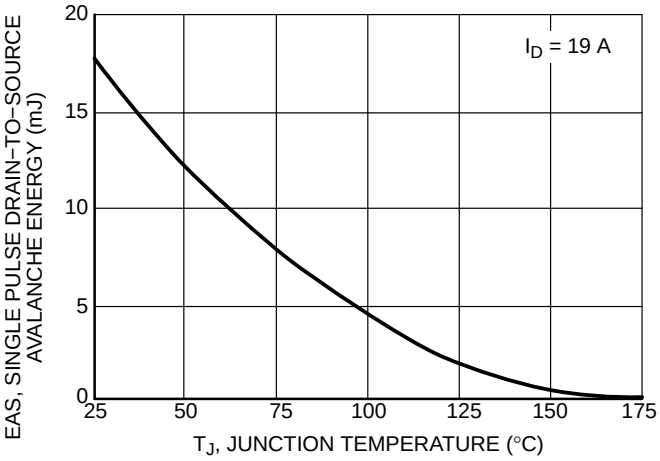


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

TYPICAL PERFORMANCE CURVES

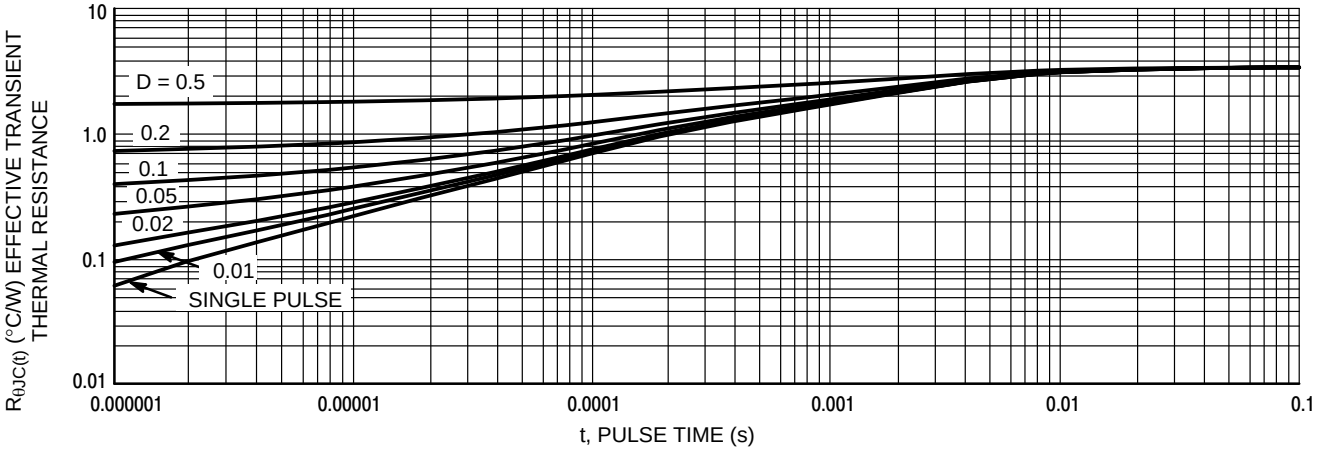


Figure 13. Thermal Response

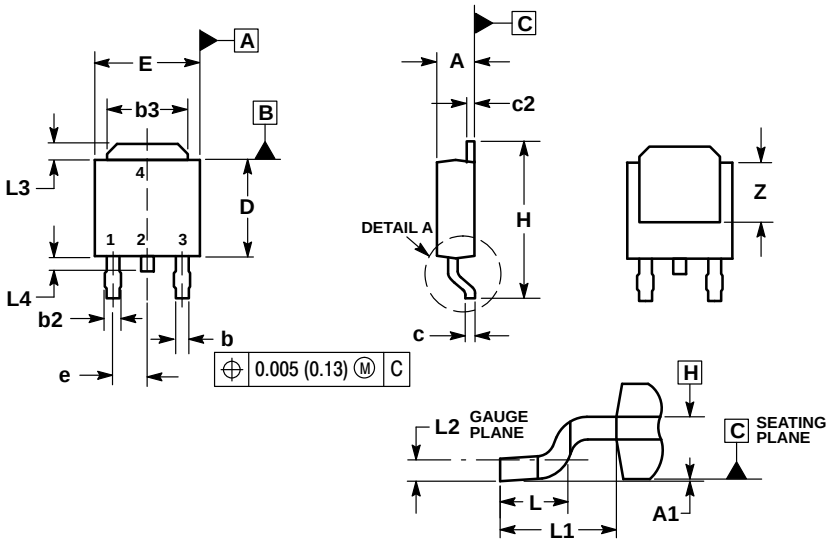
ORDERING INFORMATION

Order Number	Package	Shipping†
NVD5867NLT4G	DPAK (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

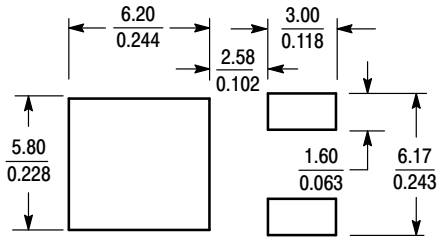
DPAK
CASE 369AA
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIMETERS	
DIM	**MIN**	**MAX**	**MIN**	**MAX**
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	−−−	0.040	−−−	1.01
Z	0.155	−−−	3.93	−−−

SOLDERING FOOTPRINT*



SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
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Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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Phone: 421 33 790 2910
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